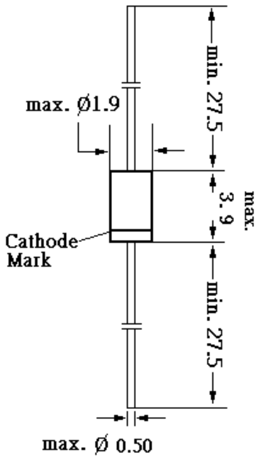
1SS83

SILICON EPITAXIAL PLANAR DIODE

High Voltage Switching



Glass case JEDEC DO-35

Dimensions in mm

Features

- High reverse voltage. (V_R = 250V)
- High reliability with glass seal.

Absolute Maximum Ratings (T_a = 25°C)

	Symbol	Value	Unit
Peak reverse voltage	V_{RM} 1)	300	V
Reverse voltage	V_R	250	V
Peak forward current	I_{FM}	625	mA
Non-Repetitive peak forward surge current	I_{FSM} 2)	1	A
Average forward current	I_O	200	mA
Power dissipation	P_{tot}	400	mW
Junction temperature	T_j	175	°C
Storage temperature	T_S	-65 to +175	°C

Notes: (1) Reverse voltage in excess of peak reverse voltage may deteriorate electrical characteristic.
(2) Within 1s forward surge current.

Characteristics at T_a = 25°C

	Symbol	Min.	Typ.	Max.	Unit
Forward voltage at I_F = 100mA	V_F	-	-	1	V
Reverse current at V_R = 250V at V_R = 300V	I_{R1} I_{R2}	- -	- -	0.2 100	µA µA
Capacitance at f = 1MHz	C	-	1.5	-	pF
Reverse recovery time at $I_F = I_R$ = 30mA, Irr = 3mA, R_L = 100Ω	t_{rr}	-	-	100	ns